

1 1. A method comprising:
2 defining a pair of spaced apart floating gates
3 over a substrate;
4 forming a stacked control gate over each floating
5 gate; and
6 forming a drain and a pair of sources by
7 implantation using said stacked control gates as a mask.

1 2. The method of claim 1 including using said
2 control gates to protect said floating gates from said
3 implantation.

1 3. The method of claim 1 including self-aligning
2 said sources and drain to both of said control gates.

1 4. The method of claim 1 including using substrate
2 hot electron injection to charge said floating gates.